ABSTRACT OF THE DISCLOSURE

A MOS transistor of the present invention comprises a gate insulating film disposed on the surface of a silicon substrate, a p-type gate electrode formed on the gate insulating film, and sidewalls formed on both sides of the gate insulating film and the gate electrode. A pair of p-type source/drain areas is provided in surface portions of the silicon substrate, and a channel area is located between the source/drain areas. The gate insulating film comprises a central portion and both end portions located on both sides of the central portion. The central portion is formed of a nitride insulating film containing at least nitrogen, and both end portions are each formed of an oxide insulating film containing oxygen and no nitrogen. The source/drain areas comprise lightly doped source/drain areas located on inner sides in contact with the channel area and deeply doped source/drain areas located on the outer sides of the lightly doped source/drain areas to form an LDD structure.